

# **PRODUCT DATA SHEET**



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Datasheet

s Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.

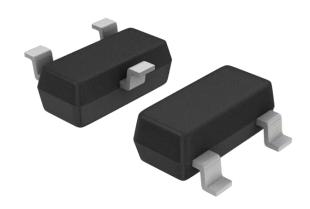




**ESD Protection Diode Array** 

### **Features**

- 350 Watts peak pulse power (tp =  $8/20\mu$ s)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2  $\pm 30$ kV contact  $\pm 30$ kV air
- IEC 61000-4-4 (EFT) 40A(5/50ns)
- IEC 61000-4-5 (Lightning) 17A(8/20μs)



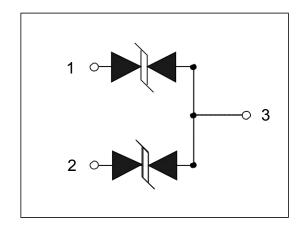
## **Applications**

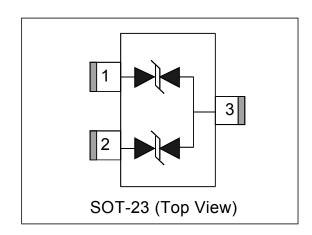
- Dataline
- Automatic Teller Machines
- Net works
- Power line

### **Mechanical Data**

- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## **Schematic & PIN Configuration**







**Absolute Maximum Rating** 

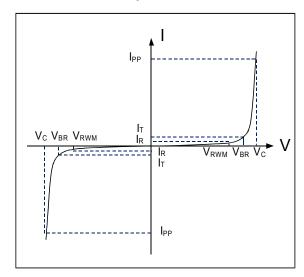
Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	350	Watts
Peak Pulse Current (t <sub>p</sub> =8/20μs)(note1)	$I_{pp}$	17	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$ m V_{ESD}$	30 30	kV
Lead Soldering Temperature	$T_{ m L}$	260(10seconds)	$^{\circ}$ C
Junction Temperature	TJ	-55 to + 125	$^{\circ}$ C
Storage Temperature	$T_{\text{stg}}$	-55 to + 125	$^{\circ}$ C

### **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-OffVoltage	$V_{RWM}$				5	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0	7.2	8.5	V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25°C		0.1	0.5	μΑ
Peak Pulse Current	$I_{PP}$	$t_p = 8/20 \mu s$			22	A
Clamping Voltage	V <sub>C</sub>	IPP=17A,tp=8/20μs			20	V
Junction Capacitance	C <sub>j</sub>	$V_R = 0V, f = 1MHz$ (Pin1 \cdot Pin2 to Pin3)		65	75	pF

# **Electrical Parameters (TA = 25°C unless otherwise noted)**

Symbol	Parameter		
Ірр	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ Ipp		
Vrwm	Working Peak Reverse Voltage		
Ir	Maximum Reverse Leakage Current @ VRWM		
V <sub>BR</sub>	Breakdown Voltage @ IT		
Iτ	Test Current		





## **TypicalCharacteristics**

Figure 1: Peak Pulse Power vs. Pulse Time

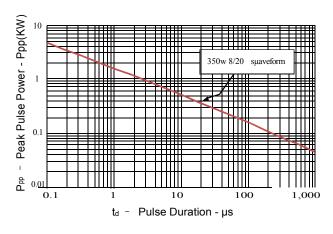


Figure 2: Power Derating Curve

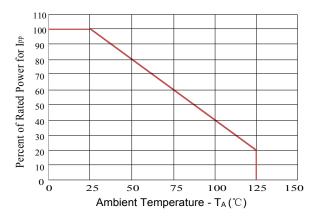


Figure3: Pulse Waveform

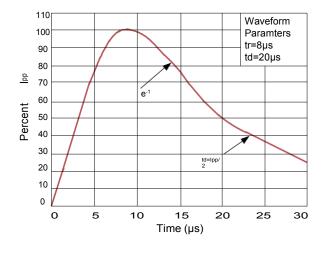
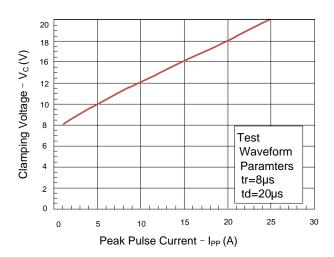


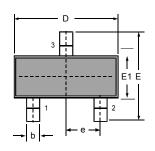
Figure 4: Clamping Voltage vs.lpp

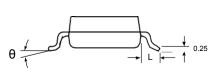






# **Outline Drawing - SOT-23**







DIMENSIONS						
SYMBOL	MILLIMETER		INCHES			
	MIN	MAX	MIN	MAX		
Α	0.900	1.150	0.035	0.045		
A1	0.000	0.100	0.000	0.004		
A2	0.900	1.050	0.035	0.041		
D	2.800	3.000	0.110	0.118		
b	0.300	0.500	0.012	0.020		
Е	2.250	2.550	0.089	0.100		
E1	1.200	1.400	0.047	0.055		
е	0.950 BSC		0.037 BSC			
L	0.300	0.500	0.012	0.020		
θ	0	8°	0	8°		



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